

General Description

The HSS1N20 is the high cell density trench N-ch MOSFETs, which provides excellent RDSON and efficiency for most of the small power switching and load switch applications.

The HSS1N20 meets the RoHS and Green Product requirement with full function reliability approved.

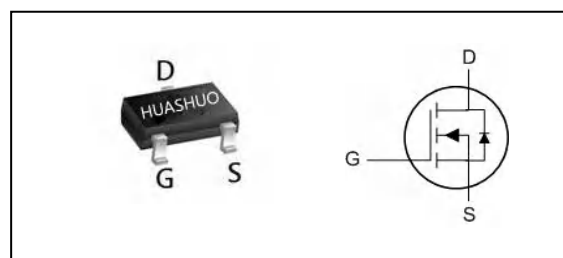
Features

- Green Device Available
- Super Low Gate Charge
- Excellent Cdv/dt effect decline
- Advanced high cell density Trench Technology

Product Summary

V_{DS}	200	V
$R_{DS(ON),Max}$	1.9	Ω
I_D	1	A

SOT-23L Pin Configuration



Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	200	V
V_{GS}	Gate-Source Voltage	± 30	V
$I_D@T_A=25^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V^1$	1	A
$I_D@T_A=70^\circ\text{C}$	Continuous Drain Current, $V_{GS} @ 10V^1$	0.8	A
I_{DM}	Pulsed Drain Current ²	6	A
$P_D@T_A=25^\circ\text{C}$	Total Power Dissipation ³	0.71	W
T_{STG}	Storage Temperature Range	-55 to 150	$^\circ\text{C}$
T_J	Operating Junction Temperature Range	-55 to 150	$^\circ\text{C}$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Thermal Resistance Junction-ambient ¹	---	125	$^\circ\text{C/W}$
$R_{\theta JC}$	Thermal Resistance Junction-Case ¹	---	80	$^\circ\text{C/W}$

Electrical Characteristics ($T_J=25^\circ\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V, I_D=250\mu A$	200	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance ²	$V_{GS}=10V, I_D=1A$	---	1.65	1.9	Ω
		$V_{GS}=4.5V, I_D=0.8A$	---	1.85	2.2	Ω
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}, I_D=250\mu A$	1.0	1.7	2.5	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=200V, V_{GS}=0V, T_J=25^\circ\text{C}$	---	---	1	μA
		$V_{DS}=200V, V_{GS}=0V, T_J=55^\circ\text{C}$	---	---	5	
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V, V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=15V, I_D=1A$	---	8	---	S
Q_g	Total Gate Charge (10V)	$V_{DS}=100V, V_{GS}=10V, I_D=1A$	---	12	---	nC
Q_{gs}	Gate-Source Charge		---	2.3	---	
Q_{gd}	Gate-Drain Charge		---	3.8	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=100V, V_{GS}=10V, R_G=2.5\Omega$ $I_D=1A$	---	9	---	ns
T_r	Rise Time		---	11	---	
$T_{d(off)}$	Turn-Off Delay Time		---	14	---	
T_f	Fall Time		---	12	---	
C_{iss}	Input Capacitance	$V_{DS}=25V, V_{GS}=0V, f=1\text{MHz}$	---	145	---	pF
C_{oss}	Output Capacitance		---	88	---	
C_{rss}	Reverse Transfer Capacitance		---	3	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current ^{1,4}	$V_G=V_D=0V$, Force Current	---	---	1	A
V_{SD}	Diode Forward Voltage ²	$V_{GS}=0V, I_S=1A, T_J=25^\circ\text{C}$	---	---	1.2	V
t_{rr}	Reverse Recovery Time	$I_F=1A, di/dt=100A/\mu s, T_J=25^\circ\text{C}$	---	38	---	nS
Q_{rr}	Reverse Recovery Charge		---	20	---	nC

Note:

1. The data tested by surface mounted on a 1 inch² FR-4 board with 2OZ copper.
2. The data tested by pulsed, pulse width $\leq 300\mu s$, duty cycle $\leq 2\%$
3. The power dissipation is limited by 150°C junction temperature
4. The data is theoretically the same as I_D and I_{DM} , in real applications, should be limited by total power dissipation.

Typical Characteristics

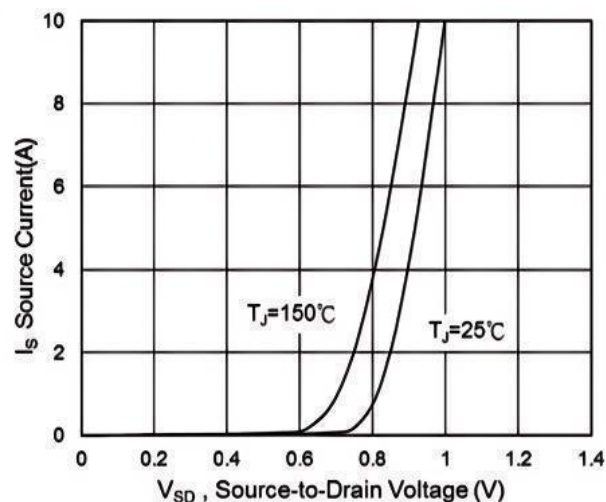


Fig.1 Forward Characteristics of Reverse

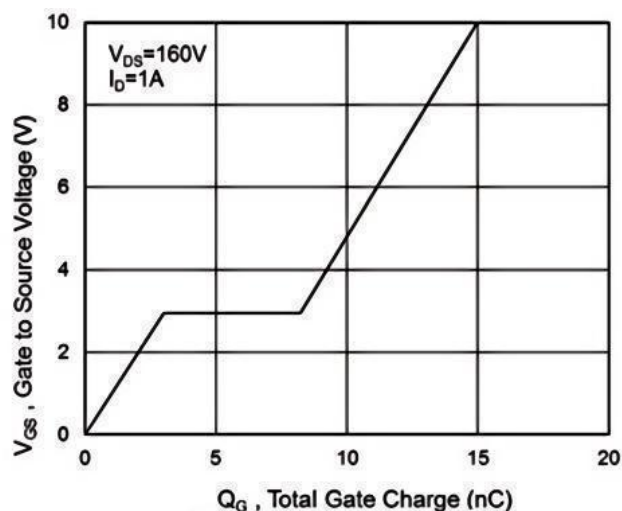


Fig.2 Gate-Charge Characteristics

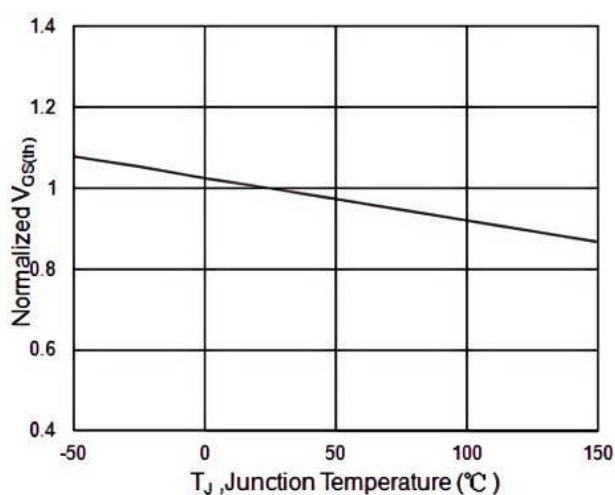


Fig.3 $V_{GS(th)}$ vs T_J

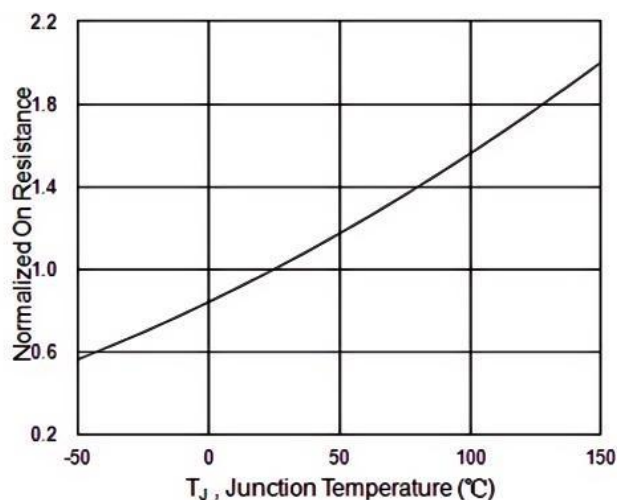


Fig.4 Normalized $R_{DS(on)}$ vs T_J

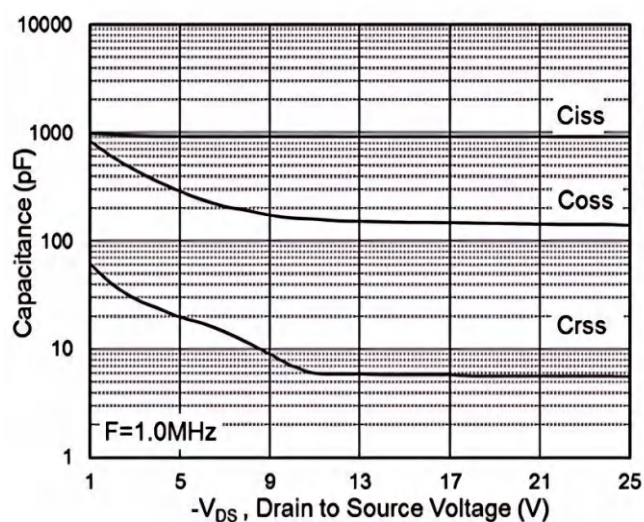


Fig.5 Capacitance

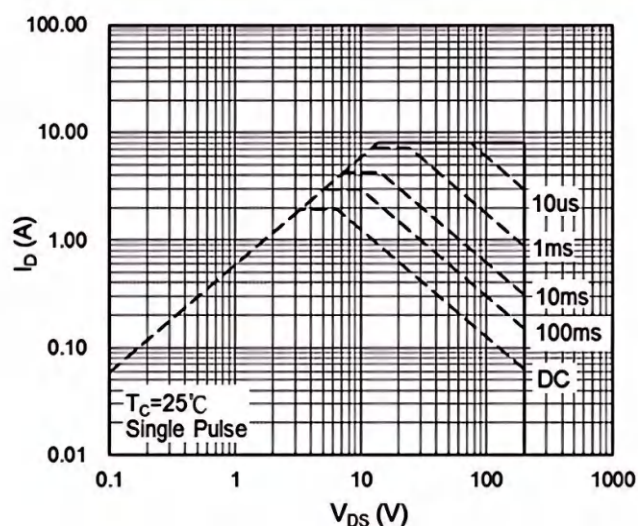


Fig.6 Safe Operating Area

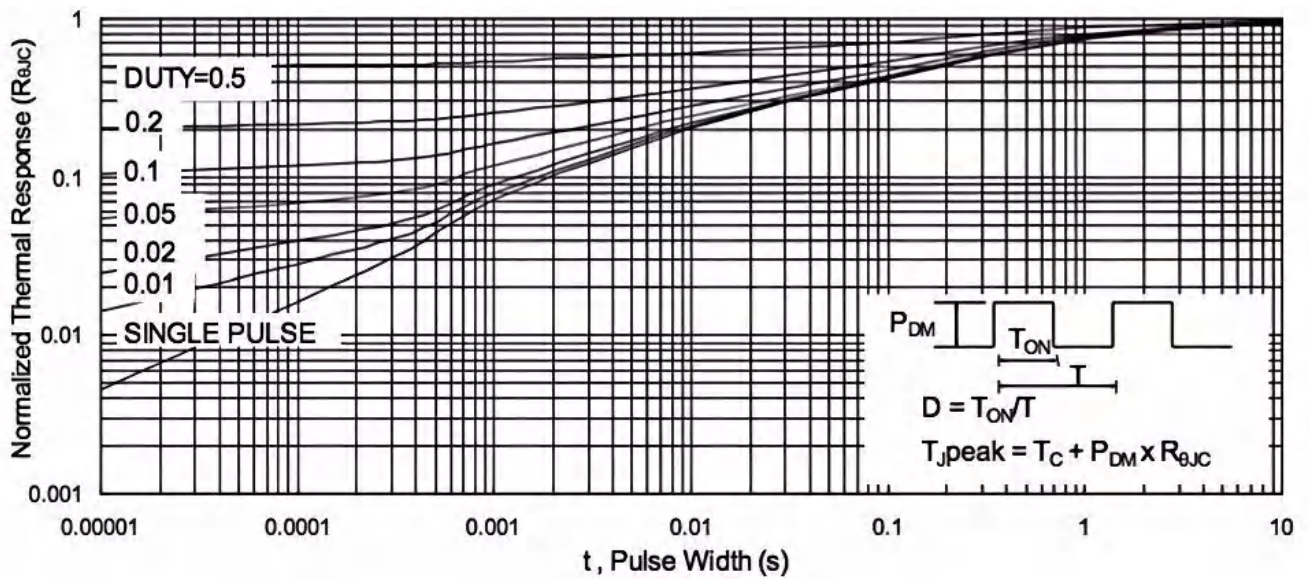


Fig.7 Normalized Maximum Transient Thermal Impedance

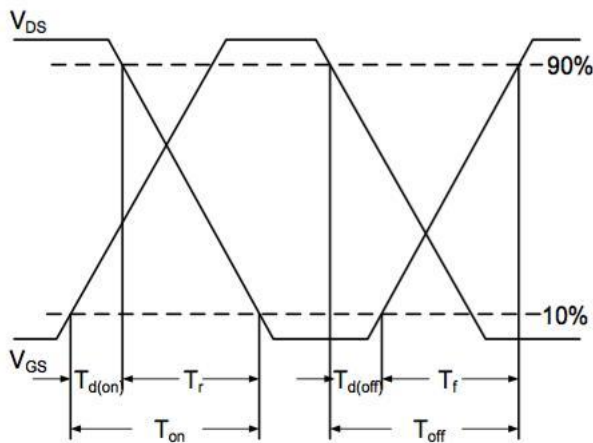


Fig.8 Switching Time Waveform

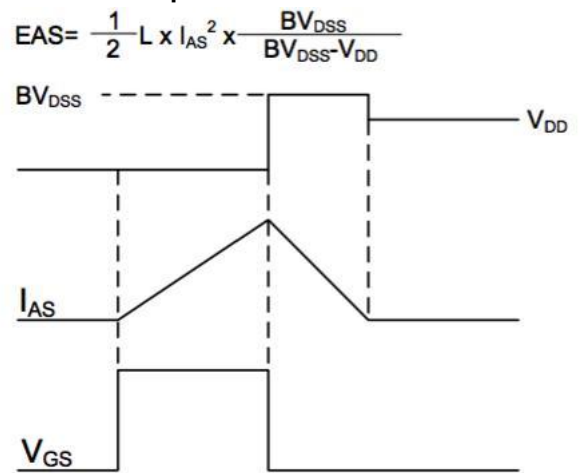


Fig.9 Gate Charge Waveform

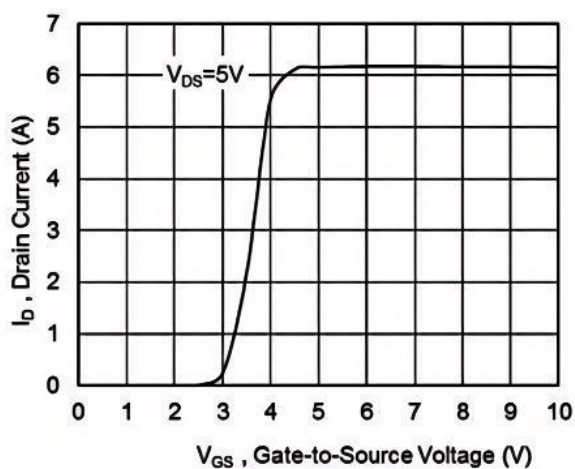
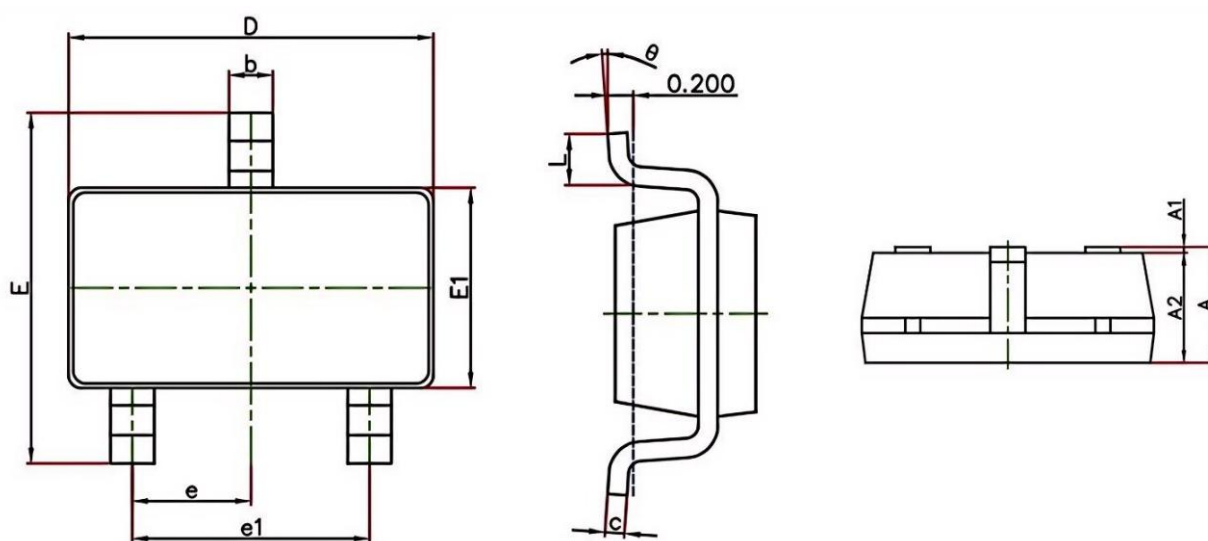


Fig.10 Transfer Characteristics

Ordering Information

Part Number	Package code	Packaging
HSS1N20	SOT-23L	3000/Tape&Reel

SOT-23L Package Outline



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	1.050	1.250	0.041	0.049
A1	0.000	0.100	0.000	0.004
A2	1.050	1.150	0.041	0.045
b	0.300	0.500	0.012	0.020
C	0.100	0.200	0.004	0.008
D	2.820	3.020	0.111	0.119
E1	1.500	1.700	0.059	0.067
E	2.650	2.950	0.104	0.116
e	0.950(BSC)		0.037(BSC)	
e1	1.800	2.000	0.071	0.079
L	0.300	0.600	0.012	0.024
θ	0°	8°	0°	8°

HSS1N20 TOP Marking

